

YJ Planar Schottky Barrier Diode Die Specification

60V 0.5A, 23mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB023L060AS-180A

Main Products Characteristics

Maximum Ratings

Symbol	Unit	Value
I_F	A	0.5
I_{RMS}	A	0.5
I_{SM}	A	1.0
T_J	°C	175
T_{stg}	°C	-55 ~ 175
T_{sol}	°C	250
T_{sld}	°C	300
T_{wld}	°C	350
T_{wld}	°C	400
T_{wld}	°C	450
T_{wld}	°C	500
T_{wld}	°C	550
T_{wld}	°C	600
T_{wld}	°C	650
T_{wld}	°C	700
T_{wld}	°C	750
T_{wld}	°C	800
T_{wld}	°C	850
T_{wld}	°C	900
T_{wld}	°C	950
T_{wld}	°C	1000

Device Schematics and Outline Drawing

Symbol	Unit	Value
I_F	A	0.5
I_{RMS}	A	0.5
I_{SM}	A	1.0
T_J	°C	175
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T_{wld}	°C	650
T_{wld}	°C	700
T_{wld}	°C	750
T_{wld}	°C	800
T_{wld}	°C	850
T_{wld}	°C	900
T_{wld}	°C	950
T_{wld}	°C	1000

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.

YangjieElectronics does not guarantee device performance after assembly.
All operating parameters must be validated for each customer application by customer's technical experts.

Data sheet information is subjected to change without notice.